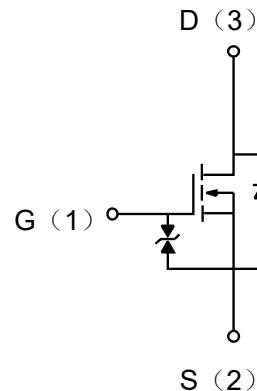


Description

PNM523T30V01 is designed for high speed switching applications

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary			
V _{DS} (V)	R _{DS(on)} (Ω)	V _{GS(th)} (V)	I _D (A)
30	7@ V _{GS} =2.5V, I _D =10mA	0.5 to 1.5	0.1



Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	V _{DSS}	I _D =10μA, V _{GS} =0V	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V	-	-	±1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	-	1.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =1mA		6.5	9	Ω
		V _{GS} =2.5V, I _D =10mA		7	9	Ω
		V _{GS} =4V, I _D =10mA	-	4	6	Ω
		V _{GS} =10V, I _D =100mA	-	3	5	Ω
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =0.1A	-	0.2	-	S
Source-Drain Diode Forward Voltage	V _{FSD} (V)	I _D =100mA, V _{GS} =0V		0.75	1	V
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1MHz	-	-	40	pF
Output Capacitance	C _{OSS}		-	-	10	pF
Reverse Transfer Capacitance	C _{RSS}		-	-	5	pF

Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
SWITCHING PARAMETERS						
Total Gate Charge	Qg	$V_{GS}=4.5V$, $V_{DS}=6V$, $I_D=0.1A$			0.5	nC
Gate-Source Charge	Qgs				0.2	nC
Gate-Drain Charge	Qgd				0.2	nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=30V$, $V_{GS}=10V$, $R_G=25\Omega$, $RL=150\Omega$, $I_D=0.1A$	-	3		ns
Turn-On Rise Time	t_r		-	3.5		ns
Turn-Off Delay Time	$t_{d(off)}$		-	5		ns
Turn-On Fall Time	t_f		-	2.5		ns

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	Continuous	I_D	A
	Pulsed	I_D	A
Total Power Dissipation	$T_A=25^\circ C$	P_D	mW

Typical Characteristics

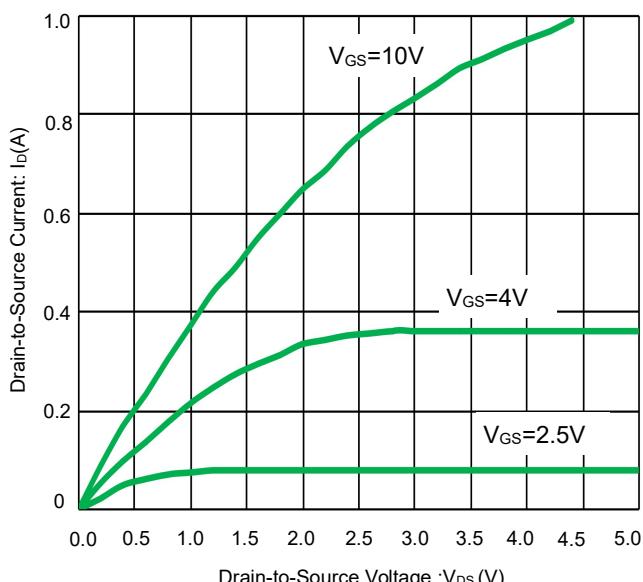


Fig 1. On-Region Characteristics

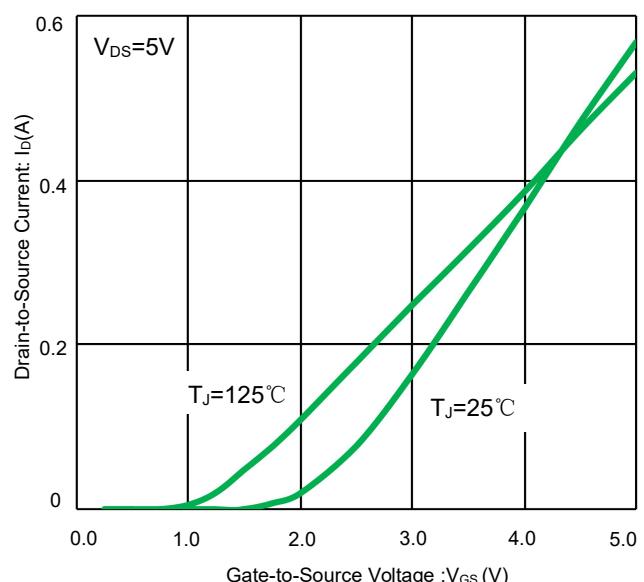


Fig 2. Transfer Characteristics

N-Channel MOSFET

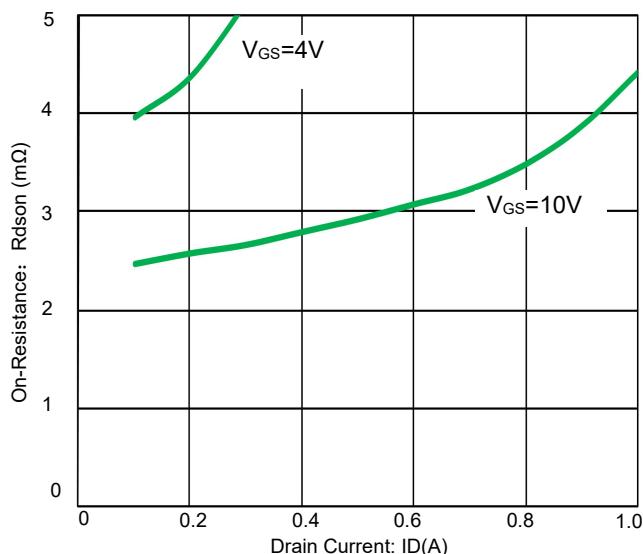


Fig 3. On-Resistance v.s. Drain Current and Gate Voltage

PNM523T30V01

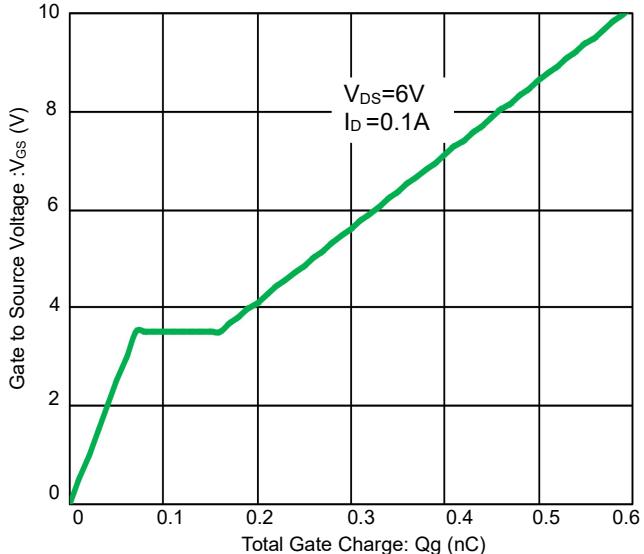


Fig 4. Gate Charge Characteristics

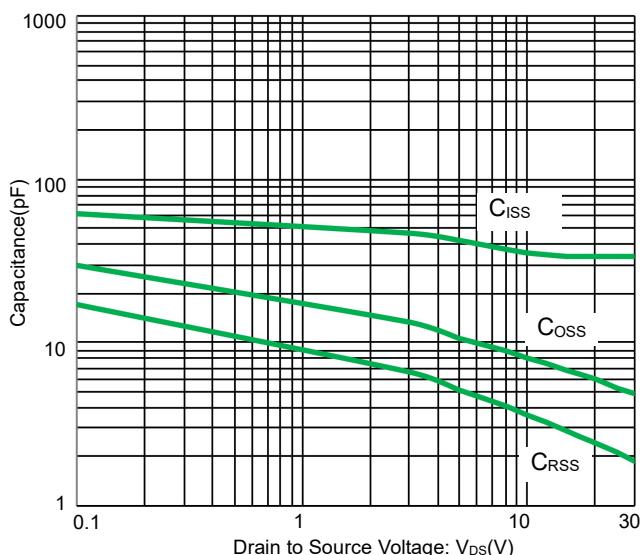


Fig 5. Capacitance Characteristic

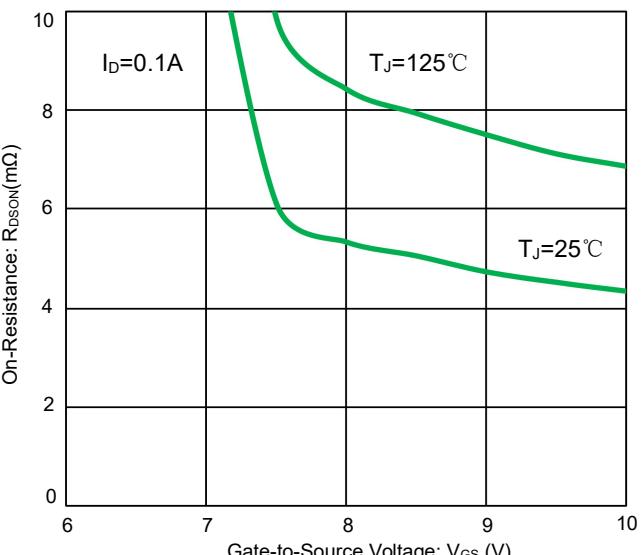


Fig 6. On-Resistance vs. Gate-to-Source Voltage

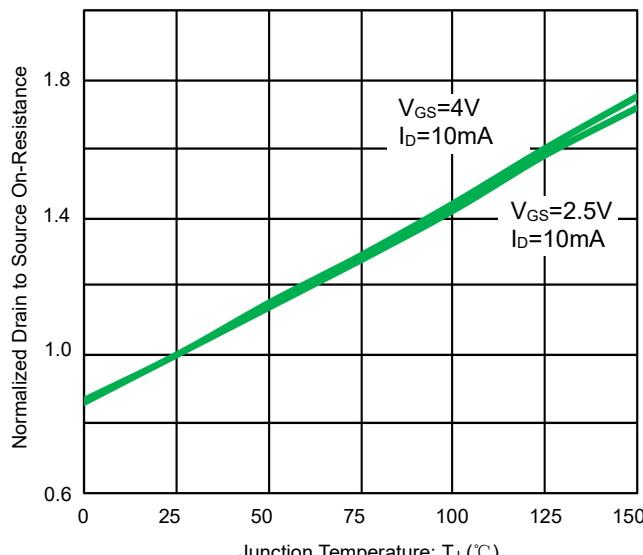


Fig 7. Normalized On-Resistance vs. Junction Temperature

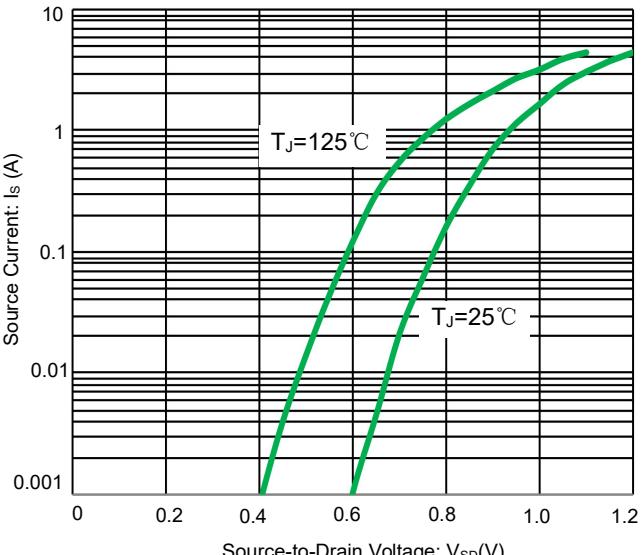
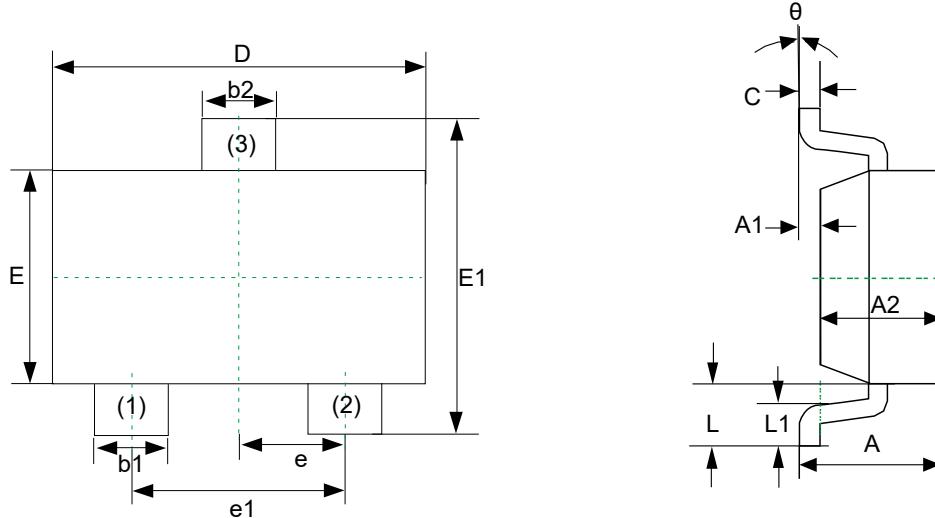
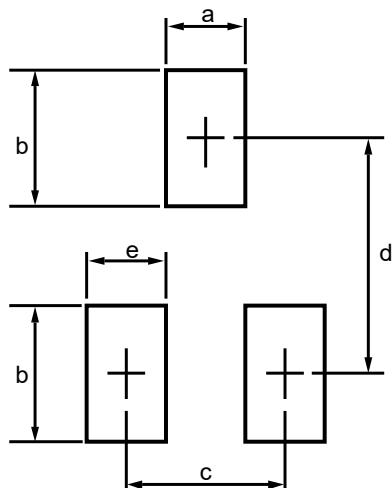


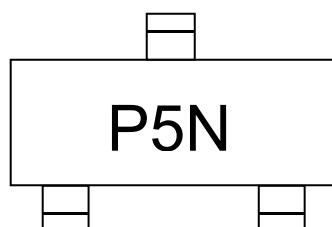
Fig 8. Body diode forward voltage

Product dimension (SOT-523)


Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500TYP		0.020TYP	
e1	0.900	1.100	0.035	0.043
L	0.400REF		0.016REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Product dimension (SOT-523)

Dim	Millimeters	
	MIN	MAX
a	--	0.5
b	--	0.6
c	--	1.0
d	--	1.24
e	--	0.4

Suggested PCB Layout**Marking information****Ordering information**

Device	Package	Reel	Shipping
PNM523T30V01	SOT-523 (Pb-Free)	7"	3000 / Tape & Reel

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